

2016 Joint International EUROSIO Workshop and International Conference on Ultimate Integration on Silicon (EUROSIO-ULIS 2016)

**Wien, Vienna, Austria
25 – 27 January 2016**



IEEE Catalog Number: CFP1649D-POD
ISBN: 978-1-4673-8610-4

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IEEE Catalog Number:	CFP1649D-POD
ISBN (Print-On-Demand):	978-1-4673-8610-4
ISBN (Online):	978-1-4673-8609-8

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